## Quad 2-Input OR Gate

## MC74VHC32

The MC74VHC32 is an advanced high speed CMOS 2-input OR gate fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7.0 V , allowing the interface of 5.0 V systems to 3.0 V systems.

## Features

- High Speed: $\mathrm{t}_{\mathrm{PD}}=3.8 \mathrm{~ns}(\mathrm{Typ})$ at $\mathrm{V}_{\mathrm{CC}}=5.0 \mathrm{~V}$
- Low Power Dissipation: $\mathrm{I}_{\mathrm{CC}}=2.0 \mu \mathrm{~A}$ (Max) at $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$
- High Noise Immunity: $\mathrm{V}_{\mathrm{NIH}}=\mathrm{V}_{\mathrm{NIL}}=28 \% \mathrm{~V}_{\mathrm{CC}}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2.0 V to 5.5 V Operating Range
- Low Noise: Volp $=0.8 \mathrm{~V}$ (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:

Human Body Model > 2000 V;
Machine Model > 200 V

- Chip Complexity: 48 FETs or 12 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are $\mathrm{Pb}-$ Free and are RoHS Compliant


Figure 1. Logic Diagram


Figure 2. Pinout: 14-Lead Packages


FUNCTION TABLE

| Inputs |  | Output |
| :---: | :---: | :---: |
| A | B | Y |
| L | L | L |
| L | H | H |
| H | L | H |
| H | H | H |

## ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
| :---: | :--- | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | DC Supply Voltage | -0.5 to +7.0 | V |
| $\mathrm{~V}_{\text {in }}$ | DC Input Voltage | -0.5 to +7.0 | V |
| $\mathrm{~V}_{\text {out }}$ | DC Output Voltage | -0.5 to $\mathrm{V}_{\mathrm{CC}}+0.5$ | V |
| $\mathrm{I}_{\mathrm{IK}}$ | Input Diode Current | -20 | mA |
| $\mathrm{I}_{\mathrm{OK}}$ | Output Diode Current | $\pm 20$ | mA |
| $\mathrm{I}_{\text {out }}$ | DC Output Current, per Pin | $\pm 25$ | mA |
| $\mathrm{I}_{\mathrm{CC}}$ | DC Supply Current, $\mathrm{V}_{\text {CC }}$ and GND Pins | $\pm 50$ | mA |
| $\mathrm{P}_{\mathrm{D}}$ | Power Dissipation in Still Air,SOIC Package  <br>   <br>   <br> $\mathrm{T}_{\text {stg }}$ Storage Temperature Package ${ }^{\dagger}$ | 500 | mW |

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, $\mathrm{V}_{\text {in }}$ and $V_{\text {out }}$ should be constrained to the range $G N D \leq\left(\mathrm{V}_{\text {in }}\right.$ or $\left.\mathrm{V}_{\text {out }}\right) \leq \mathrm{V}_{\mathrm{CC}}$. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or $\mathrm{V}_{\mathrm{CC}}$ ). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
$\dagger$ Derating - SOIC Package: $-7 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ from $65^{\circ}$ to $125^{\circ} \mathrm{C}$
TSSOP Package: $-6.1 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ from $65^{\circ}$ to $125^{\circ} \mathrm{C}$
RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter |  | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | DC Supply Voltage |  | 2.0 | 5.5 | V |
| $V_{\text {in }}$ | DC Input Voltage |  | 0 | 5.5 | V |
| $V_{\text {out }}$ | DC Output Voltage |  | 0 | $\mathrm{V}_{\text {CC }}$ | $\checkmark$ |
| $\mathrm{T}_{\mathrm{A}}$ | Operating Temperature |  | -40 | +125 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{tr}_{\mathrm{r}} \mathrm{t}_{\mathrm{f}}$ | Input Rise and Fall Time | $\begin{aligned} & \mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V} \pm 0.3 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{CC}}=5.0 \mathrm{~V} \pm 0.5 \mathrm{~V} \end{aligned}$ | $\begin{aligned} & 0 \\ & 0 \end{aligned}$ | $\begin{gathered} 100 \\ 20 \end{gathered}$ | ns/V |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## DC ELECTRICAL CHARACTERISTICS

| Symbol | Parameter | Test Conditions | $\begin{gathered} \mathrm{v}_{\mathrm{cc}} \\ \mathrm{~V} \end{gathered}$ | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ |  |  | $\mathrm{T}_{\mathrm{A}}=-40^{\circ} \mathrm{C}$ to $125^{\circ} \mathrm{C}$ |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | Min | Typ | Max | Min | Max |  |
| $\mathrm{V}_{\mathrm{IH}}$ | Minimum High-Level Input Voltage |  | $\begin{gathered} 2.0 \\ 3.0 \text { to } 5.5 \end{gathered}$ | $\begin{gathered} 1.50 \\ v_{C C} \times 0.7 \end{gathered}$ |  |  | $\begin{gathered} 1.50 \\ v_{C C} \times 0.7 \end{gathered}$ |  | V |
| $\mathrm{V}_{\mathrm{IL}}$ | Maximum Low-Level Input Voltage |  | $\begin{gathered} 2.0 \\ 3.0 \text { to } 5.5 \end{gathered}$ |  |  | $\begin{gathered} 0.50 \\ \mathrm{~V}_{\mathrm{CC}} \times 0.3 \end{gathered}$ |  | $\begin{gathered} 0.50 \\ v_{C C} \times 0.3 \end{gathered}$ | V |
| $\mathrm{V}_{\mathrm{OH}}$ | Minimum High-Level Output Voltage | $\begin{aligned} & \mathrm{V}_{\text {in }}=\mathrm{V}_{\mathrm{IH}} \text { or } \mathrm{V}_{\mathrm{IL}} \\ & \mathrm{I}_{\mathrm{OH}}=-50 \mu \mathrm{~A} \end{aligned}$ | $\begin{aligned} & 2.0 \\ & 3.0 \\ & 4.5 \end{aligned}$ | $\begin{aligned} & 1.9 \\ & 2.9 \\ & 4.4 \end{aligned}$ | $\begin{aligned} & 2.0 \\ & 3.0 \\ & 4.5 \end{aligned}$ |  | $\begin{aligned} & 1.9 \\ & 2.9 \\ & 4.4 \end{aligned}$ |  | V |
|  |  | $\begin{aligned} & \mathrm{V}_{\text {in }}=\mathrm{V}_{\mathrm{IH}} \text { or } \mathrm{V}_{\mathrm{IL}} \\ & \mathrm{I}_{\mathrm{OH}}=-4.0 \mathrm{~mA} \\ & \mathrm{I}_{\mathrm{OH}}=-8.0 \mathrm{~mA} \end{aligned}$ | $\begin{aligned} & 3.0 \\ & 4.5 \end{aligned}$ | $\begin{aligned} & 2.58 \\ & 3.94 \end{aligned}$ |  |  | $\begin{aligned} & 2.48 \\ & 3.80 \end{aligned}$ |  |  |
| $\mathrm{V}_{\text {OL }}$ | Maximum Low-Level Output Voltage | $\begin{aligned} & \mathrm{V}_{\text {in }}=\mathrm{V}_{\mathrm{IH}} \text { or } \mathrm{V}_{\mathrm{IL}} \\ & \mathrm{l}_{\mathrm{OL}}=50 \mu \mathrm{~A} \end{aligned}$ | $\begin{aligned} & 2.0 \\ & 3.0 \\ & 4.5 \end{aligned}$ |  | $\begin{aligned} & 0.0 \\ & 0.0 \\ & 0.0 \end{aligned}$ | $\begin{aligned} & 0.1 \\ & 0.1 \\ & 0.1 \end{aligned}$ |  | $\begin{aligned} & 0.1 \\ & 0.1 \\ & 0.1 \end{aligned}$ | V |
|  |  | $\begin{aligned} & \mathrm{V}_{\mathrm{in}}=\mathrm{V}_{\mathrm{IH}} \text { or } \mathrm{V}_{\mathrm{IL}} \\ & \mathrm{I}_{\mathrm{OL}}=4.0 \mathrm{~mA} \\ & \mathrm{I}_{\mathrm{OL}}=8.0 \mathrm{~mA} \end{aligned}$ | $\begin{aligned} & 3.0 \\ & 4.5 \end{aligned}$ |  |  | $\begin{aligned} & 0.36 \\ & 0.36 \end{aligned}$ |  | $\begin{aligned} & 0.44 \\ & 0.44 \end{aligned}$ |  |
| $\mathrm{l}_{\text {in }}$ | Maximum Input Leakage Current | $\mathrm{V}_{\text {in }}=5.5 \mathrm{~V}$ or GND | 0 to 5.5 |  |  | $\pm 0.1$ |  | $\pm 1.0$ | $\mu \mathrm{A}$ |
| $\mathrm{I}_{\mathrm{Cc}}$ | Maximum Quiescent Supply Current | $\mathrm{V}_{\text {in }}=\mathrm{V}_{\text {CC }}$ or GND | 5.5 |  |  | 2.0 |  | 20.0 | $\mu \mathrm{A}$ |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## MC74VHC32

AC ELECTRICAL CHARACTERISTICS (Input $\mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=3.0 \mathrm{~ns}$ )

| Symbol | Parameter | Test Conditions | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ |  |  | $\mathrm{T}_{\mathrm{A}}=-40^{\circ} \mathrm{C}$ to $125^{\circ} \mathrm{C}$ |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | Min | Typ | Max | Min | Max |  |
| $\begin{aligned} & \mathrm{t}_{\mathrm{PLH}}, \\ & \mathrm{t}_{\mathrm{PH}} \end{aligned}$ | Maximum Propagation Delay, A or B to Y | $\begin{aligned} \mathrm{V}_{\mathrm{CC}}=3.3 \pm 0.3 \mathrm{VC}_{\mathrm{L}} & =15 \mathrm{pF} \\ \mathrm{C}_{\mathrm{L}} & =50 \mathrm{pF} \end{aligned}$ |  | $\begin{aligned} & 5.5 \\ & 8.0 \end{aligned}$ | $\begin{gathered} \hline 7.9 \\ 11.4 \end{gathered}$ | $\begin{aligned} & 1.0 \\ & 1.0 \end{aligned}$ | $\begin{gathered} \hline 9.5 \\ 13.0 \end{gathered}$ | ns |
|  |  | $\begin{aligned} \mathrm{V}_{\mathrm{CC}}=5.0 \pm 0.5 \mathrm{VC}_{\mathrm{L}} & =15 \mathrm{pF} \\ \mathrm{C}_{\mathrm{L}} & =50 \mathrm{pF} \end{aligned}$ |  | $\begin{aligned} & \hline 3.8 \\ & 5.3 \end{aligned}$ | $\begin{aligned} & 5.5 \\ & 7.5 \end{aligned}$ | $\begin{aligned} & \hline 1.0 \\ & 1.0 \end{aligned}$ | $\begin{aligned} & \hline 6.5 \\ & 8.5 \end{aligned}$ |  |
| $\mathrm{C}_{\text {in }}$ | Maximum Input Capacitance |  |  | 4 | 10 |  | 10 | pF |


|  |  | Typical @ 25 ${ }^{\circ} \mathbf{C}, \mathbf{V}_{\mathbf{C C}}=\mathbf{5 . 0} \mathbf{V}$ |  |
| :--- | :--- | :---: | :---: |
| $\mathrm{C}_{\mathrm{PD}}$ | Power Dissipation Capacitance (Note 1) | 14 | pF |

1. $\mathrm{C}_{\mathrm{PD}}$ is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{C C(O P R)}=C_{P D} \bullet V_{C C} \bullet f_{i n}+I_{C C} / 4$ (per gate). $C_{P D}$ is used to determine the no-load dynamic power consumption; $\mathrm{P}_{\mathrm{D}}=\mathrm{C}_{\mathrm{PD}} \bullet \mathrm{V}_{\mathrm{CC}}{ }^{2} \bullet \mathrm{f}_{\mathrm{in}}+\mathrm{I}_{\mathrm{CC}} \bullet \mathrm{V}_{\mathrm{CC}}$.

NOISE CHARACTERISTICS (Input $\mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=3.0 \mathrm{~ns}, \mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}, \mathrm{V}_{\mathrm{CC}}=5.0 \mathrm{~V}$ )

| Symbol | Characteristic | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ |  | Unit |
| :---: | :---: | :---: | :---: | :---: |
|  |  | Typ | Max |  |
| $\mathrm{V}_{\text {OLP }}$ | Quiet Output Maximum Dynamic $\mathrm{V}_{\text {OL }}$ | 0.3 | 0.8 | V |
| $\mathrm{V}_{\text {OLV }}$ | Quiet Output Minimum Dynamic $\mathrm{V}_{\text {OL }}$ | -0.3 | -0.8 | V |
| $\mathrm{V}_{\text {IHD }}$ | Minimum High Level Dynamic Input Voltage |  | 3.5 | V |
| $\mathrm{V}_{\text {ILD }}$ | Maximum Low Level Dynamic Input Voltage |  | 1.5 | V |



Figure 3. Switching Waveforms

*Includes all probe and jig capacitance
Figure 4. Test Circuit


Figure 5. Input Equivalent Circuit

## MC74VHC32

ORDERING INFORMATION

| Device | Package | Shipping ${ }^{\dagger}$ |
| :--- | :---: | :---: |
| MC74VHC32DR2G | SOIC-14 <br> (Pb-Free) | 2500 Units / Tape \& Reel |
| NLV74VHC32DR2G |  |  |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.


SOIC-14 NB
CASE 751A-03
ISSUE L
SCALE 1:1


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR

PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE

MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

| DIM | MILLIMETERS |  | INCHES |  |
| :---: | :---: | :---: | :---: | :---: |
|  | MIN | MAX | MIN | MAX |
|  | 1.35 | 1.75 | 0.054 | 0.068 |
| A1 | 0.10 | 0.25 | 0.004 | 0.010 |
| A3 | 0.19 | 0.25 | 0.008 | 0.010 |
| b | 0.35 | 0.49 | 0.014 | 0.019 |
| D | 8.55 | 8.75 | 0.337 | 0.344 |
| E | 3.80 | 4.00 | 0.150 | 0.157 |
| e | 1.27 | BSC | 0.050 | BSC |
| H | 5.80 | 6.20 | 0.228 | 0.244 |
| h | 0.25 | 0.50 | 0.010 | 0.019 |
| L | 0.40 | 1.25 | 0.016 | 0.049 |
| M | $0^{\circ}$ | $7^{\circ}$ | $0^{\circ}$ | $7^{\circ}$ |

## SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS
*For additional information on our $\mathrm{Pb}-$ Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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STYLE 1:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. NO CONNECTION
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. NO CONNECTION
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
4. COMMON ANODE
STYLE $5:$

PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHOD
4. ANODE/CATHOD
4. ANODE/CATHODE
5. ANODE/CATHODE
6. NO CONNECTION
7. COMMON ANODE
8. COMMON CATHOD
9. ANODE/CATHODE
10. ANODE/CATHODE
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 2 :
CANCELLED

STYLE 3:
PIN 1. NO CONNECTION 2. ANODE 3. ANODE
4. NO CONNECTION 5. ANODE
6. NO CONNECTION
7. ANODE
8. ANODE
9. ANODE
10. NO CONNECTION
11. ANODE
12. ANODE
13. NO CONNECTION
14. COMMON CATHODE

## STYLE 6

PIN 1. CATHODE
2. CATHODE
3. CATHODE
4. CATHODE
5. CATHODE
5. CATHODE
6. CATHODE
7. CATHOD
8. ANODE
10. ANODE
11. ANODE
12. ANODE
13. ANODE
14. ANODE

STYLE 7:
PIN 1. ANODE/CATHODE
2. COMMON ANODE
3. COMMON CATHODE
4. ANODE/CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. ANODE/CATHODE
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. COMMON CATHODE
11. COMMON CATHOD
13. ANODE/CATHODE
14. ANODE/CATHODE

STYLE 4:
PIN 1. NO CONNECTION 2. CATHODE
3. CATHODE
4. NO CONNECTION
5. CATHODE
6. NO CONNECTION
7. CATHODE
. CATHODE
9. CATHODE
10. NO CONNECTION
11. CATHODE
12. CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 8:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
4. NO CONNECTION
5. ANODE/CATHODE
6. ANODE/CATHODE
7. COMMON ANODE
8. COMMON ANODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. NO CONNECTION
11. NO CONNECTION
12. ANODE/CATHODE
12. ANODE/CATHODE
13. ANODE/CATHODE
13. ANODE/CATHODE
14. COMMON CATHODE

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NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS MOLD FLASH OR GATE BURRS SHALL NOT MOLD FLASH OR GATE BURRS
4. DIMENSION B DOES NOT INCLUDE

INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR
PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

| DIM | MILLIMETERS |  | INCHES |  |
| :---: | :---: | :---: | :---: | :---: |
|  | MIN | MAX | MIN | MAX |
| A | 4.90 | 5.10 | 0.193 | 0.200 |
| B | 4.30 | 4.50 | 0.169 | 0.177 |
| C | --- | 1.20 | --- | 0.047 |
| D | 0.05 | 0.15 | 0.002 | 0.006 |
| F | 0.50 | 0.75 | 0.020 | 0.030 |
| G | 0.65 | BSC | 0.026 |  |
| BSC |  |  |  |  |
| H | 0.50 | 0.60 | 0.020 | 0.024 |
| J | 0.09 | 0.20 | 0.004 | 0.008 |
| J1 | 0.09 | 0.16 | 0.004 | 0.006 |
| K | 0.19 | 0.30 | 0.007 | 0.012 |
| K1 | 0.19 | 0.25 | 0.007 | 0.010 |
| L | 6.40 | BSC | 0.252 | BSC |
| M | $0{ }^{\circ}$ | $8^{\circ}$ | $0^{\circ}$ | $8^{\circ}$ |

GENERIC MARKING DIAGRAM*



| A | $=$ Assembly Location |
| :--- | :--- |
| L | $=$ Wafer Lot |
| Y | $=$ Year |
| W | $=$ Work Week |
| - | $=$ Pb-Free Package |

(Note: Microdot may be in either location)
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " $\bullet$ ", may or may not be present.

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